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NOIDA INSTITUTE OF ENGINEERING AND TECHNOLOGY, GREATER NOIDA

(An Autonomous Institute)

Affiliated to Dr. A.P.J. Abdul Kalam Technical University, Uttar Pradesh, Lucknow

M.Tech

SEM: I - THEORY EXAMINATION (2021 - 2022)

Subject: CMOS Digital VLSI Design

Time: 03:00 Hours

Max. Marks: 70

General Instructions:

1. All questions are compulsory. It comprises of three Sections A, B and C.
 - Section A - Question No- 1 is objective type question carrying 1 mark each & Question No- 2 is very short type questions carrying 2 marks each.
 - Section B - Question No- 3 is Long answer type - I questions carrying 4 marks each.
 - Section C - Question No- 4 to 8 are Long answer type - II questions carrying 7 marks each.
 - No sheet should be left blank. Any written material after a Blank sheet will not be evaluated/checked.

SECTION A

15

1. Attempt all parts:-

- 1-a. The enhancement type basically termed as normally-OFF N MOSFET works only with _____ (CO1) 1
1. large positive gate voltage
 2. large negative gate voltage
 3. large positive drain voltage
 4. . large negative drain voltage
- 1-b. In CMOS fabrication, nMOS and pMOS are integrated in same substrate. (CO2) 1
1. a) true
 2. b) false
- 1-c. The boolean function $Y=AB+CD$ is to be realized using only 2 input NAND gates. The minimum number of gates required is _____. (CO3) 1
1. 2
 2. 3
 3. 4
 4. 5
- 1-d. In precharge phase, when capacitor is fully charge it becomes equal to V_{DD} . (T/F) (CO4) 1
1. TRUE
 2. FALSE
- 1-e. Which of the following memories uses one transistor and one capacitor as basic memory unit (CO5) 1
1. SRAM
 2. DRAM
 3. Both
 4. None

2. Attempt all parts:-

- 2-a. Explain the three regions of operation of a MOSFET. (CO1) 2
- 2-b. Compare between CMOS and bipolar technologies. (CO2) 2

2-c.	Draw CMOS diagram of the function $Y=(A.(B+C))'$ (CO3)	2
2-d.	What is pass transistor? (CO4)	2
2-e.	Differentiate between SRAM and DRAM. (CO5)	2

SECTION B

20

3. Answer any five of the following:-

3-a.	Explain the energy band diagram for combined MOS system and elaborate why there is bending near the oxide semiconductor interface? (CO1)	4
3-b.	Explain accumulation, depletion, inversion regions of operation in case externally biased MOS structure.(CO1)	4
3-c.	Explain briefly the scaling in VLSI. (CO2)	4
3-d.	What is switching power dissipation of CMOS inverter? (CO2)	4
3-e.	Draw CMOS diagram of the function $Y=(A.B+C). (D+E))'$ (CO3)	4
3-f.	Explain synchronous dynamic circuit techniques with neat diagrams.(CO4)	4
3-g.	What is DRAM ? Explain DRAM with the diagram.(CO5)	4

SECTION C

35

4. Answer any one of the following:-

4-a.	What is channel length modulation? Calculate effective channel length and new drain current.(CO1)	7
4-b.	Define Noise immunity and Noise margins. Calculate V_{OH} , V_{OL} , V_{IL} , V_{IH} for a depletion-load nMOS Inverter. Explain why we don't use enhancement-load nMOS inverter? (CO1)	7

5. Answer any one of the following:-

5-a.	What is CMOS inverter? Draw the voltage transfer curve (VTC) and explain. (CO2)	7
5-b.	What is threshold voltage for CMOS inverter? Calculate Noise margin for CMOS inverter. (CO2)	7

6. Answer any one of the following:-

6-a.	Explain the design of CMOS Full Adder with the help of a neat diagram. (CO3)	7
6-b.	Draw and explain the D FF design with the help of transmission gate. (CO3)	7

7. Answer any one of the following:-

7-a.	What is dynamic CMOS transmission gate logic? Explain it with two different stages and also explain the working of soft node. (CO4)	7
7-b.	Differentiate between synchronous and asynchronous sequential circuits? What are the synchronous dynamic circuit techniques? (CO4)	7

8. Answer any one of the following:-

8-a.	Distinguish between NOR flash memory cell and NAND flash memory cell. (CO5)	7
8-b.	What do you mean by static RAM. Explain the Read and Write operations of 6 Transistor SRAM cell with a neat diagram. (CO5)	7